

Fig.1

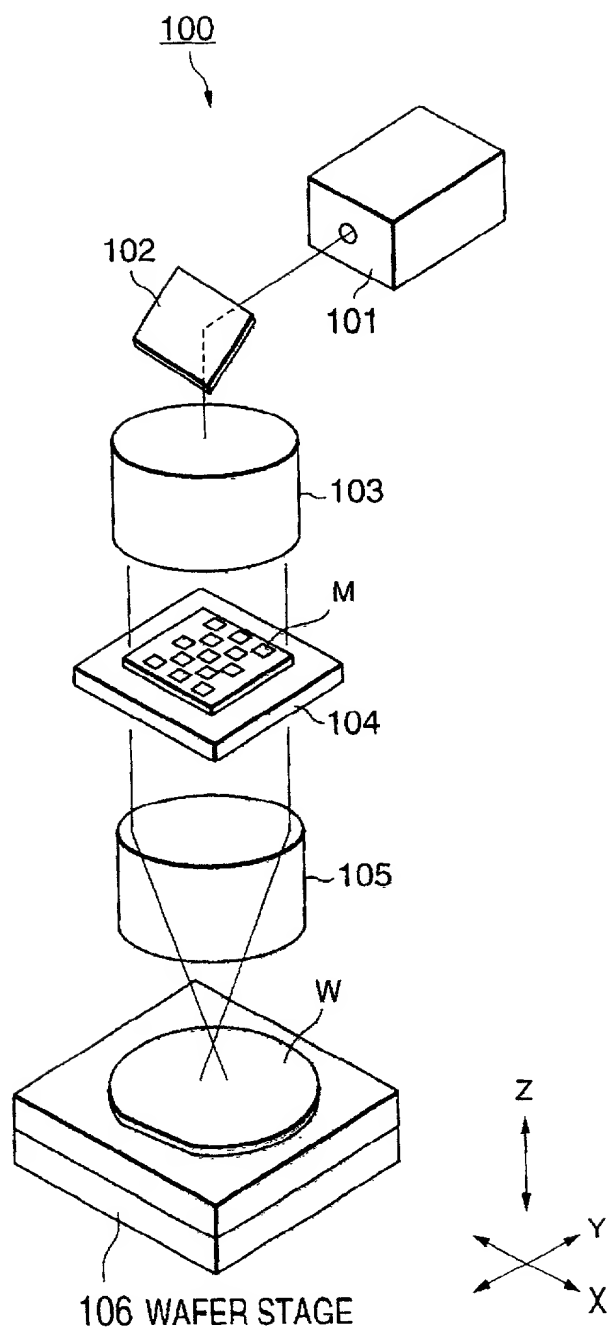
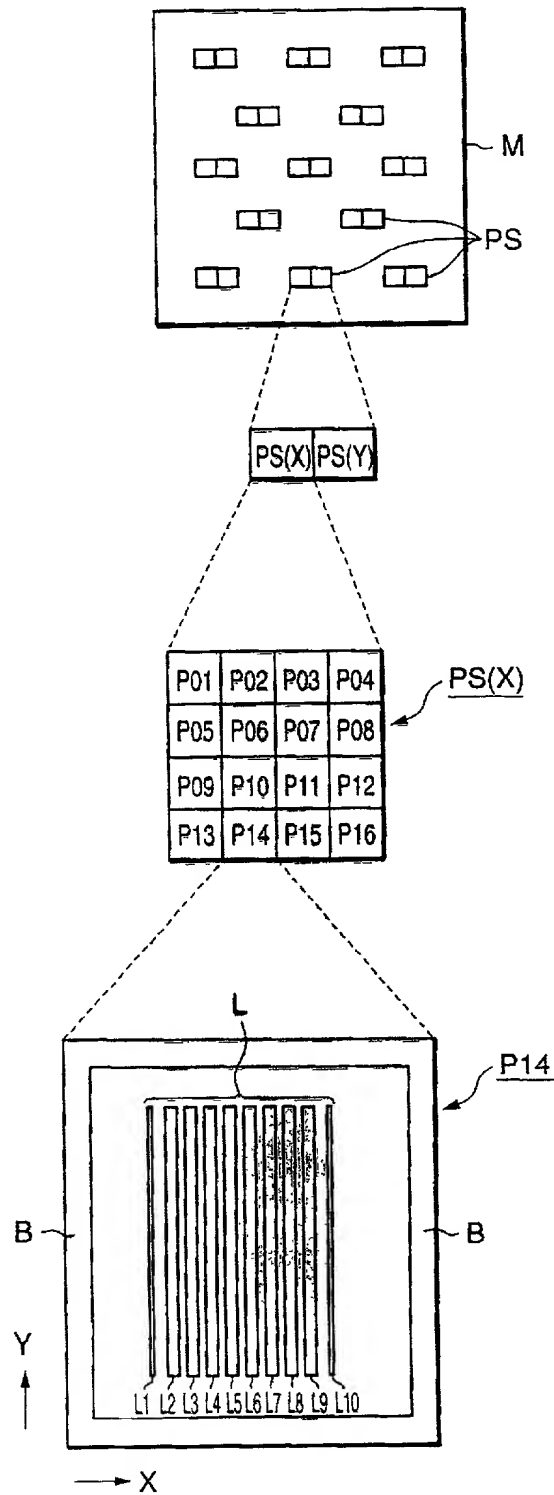


Fig.2



Top view of a device structure. The structure consists of a grid of vertical lines. The horizontal lines are labeled W1 through W10, and the vertical lines are labeled L1 through L10. The total width of the grid is 4800nm, and the total height is 3600nm. The pitch (p) is 400nm. The structure is labeled B and L.

P01	W1, W10 =200nm	// =195nm	// =190nm	// =185nm
P06	// =180nm	// =175nm	// =170nm	// =165nm
P10	// =160nm	// =155nm	// =150nm	// =145nm
P13	// =140nm	// =135nm	// =130nm	// =125nm

Fig.4

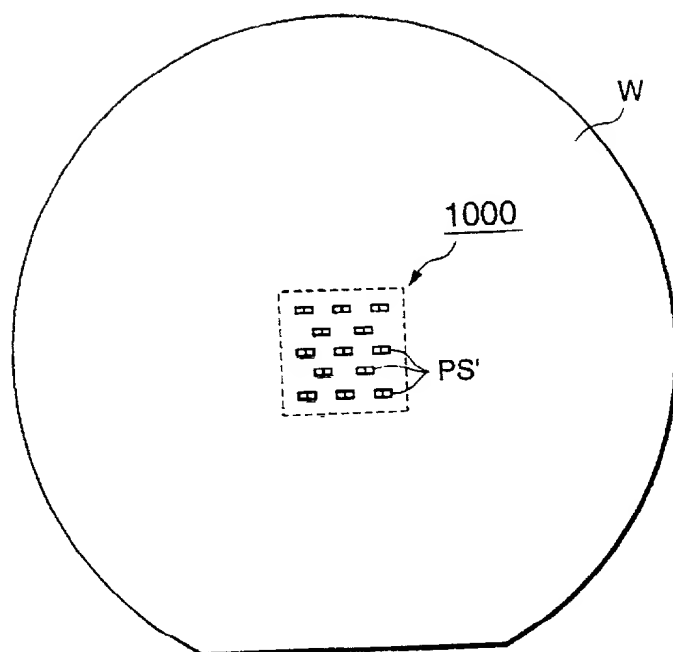


Fig.5(a)

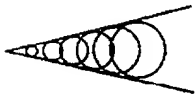


Fig.5(b)

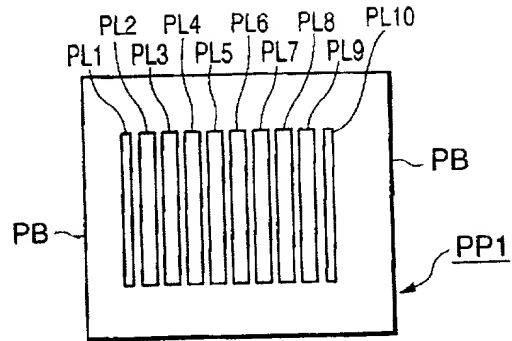


Fig.5(c)

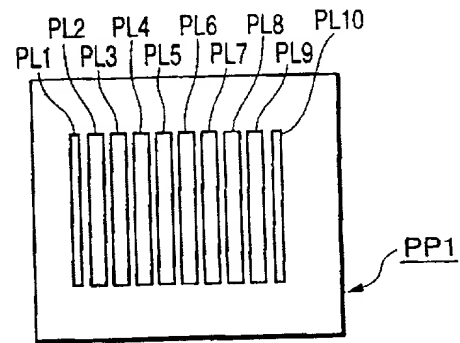


Fig.5(d)

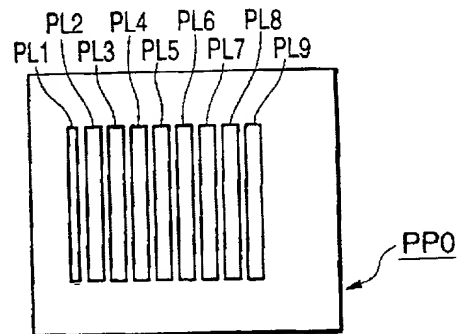


Fig.5(e)

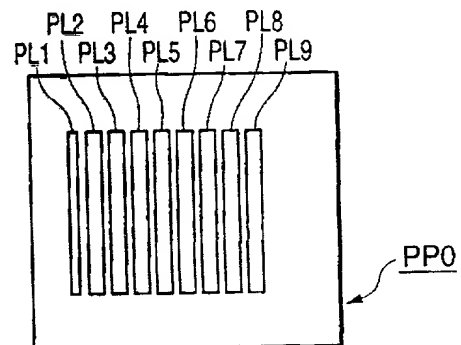


Fig.6(b)

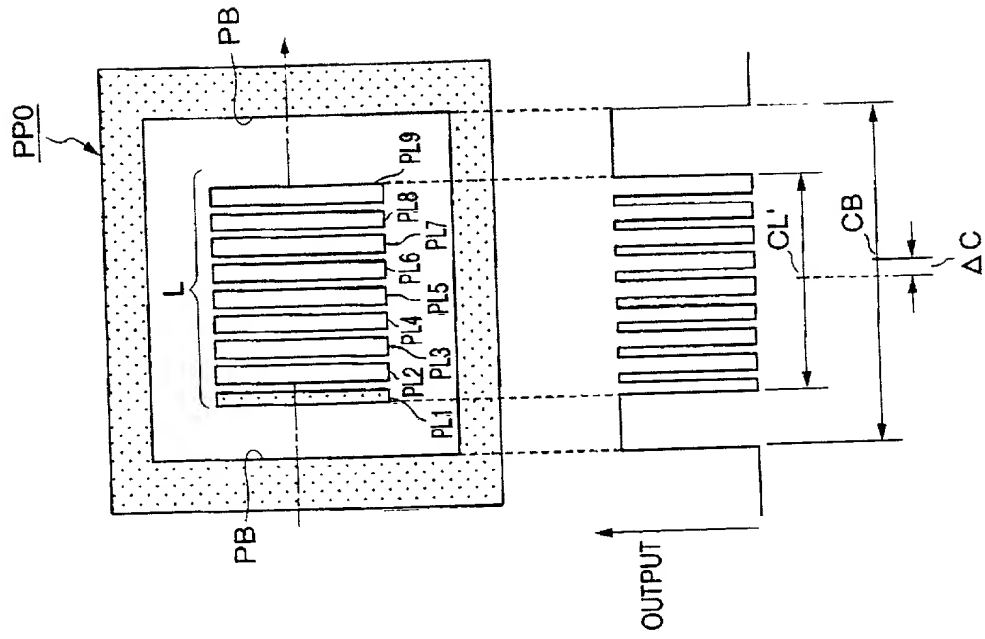


Fig.6(a)

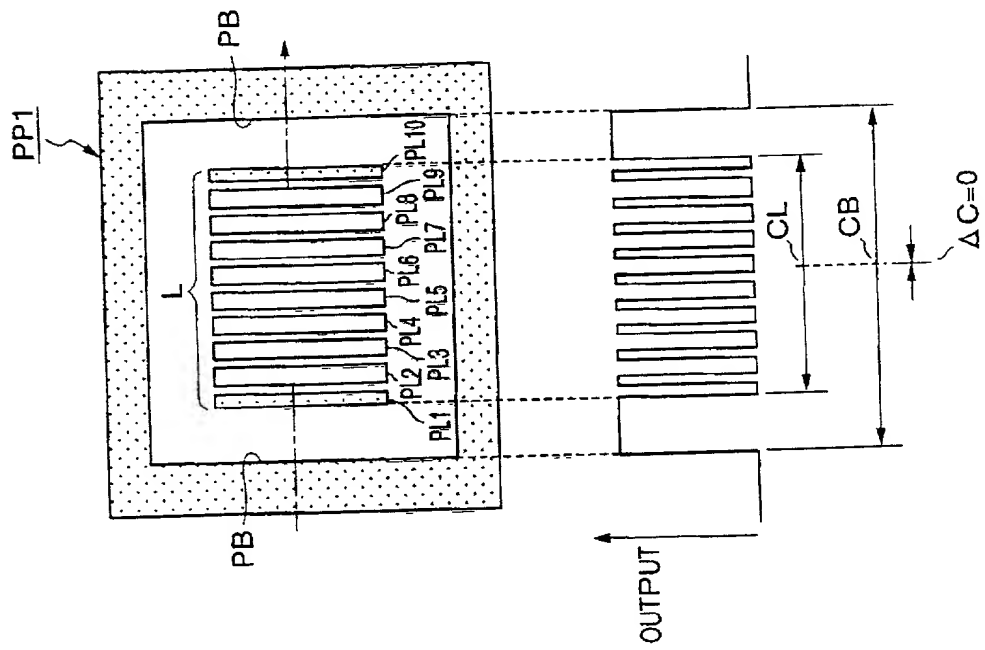


Fig.7

RELATIVE POSITIONAL DEVIATION  
(RESULT OF OVERLAY MEASUREMENT)

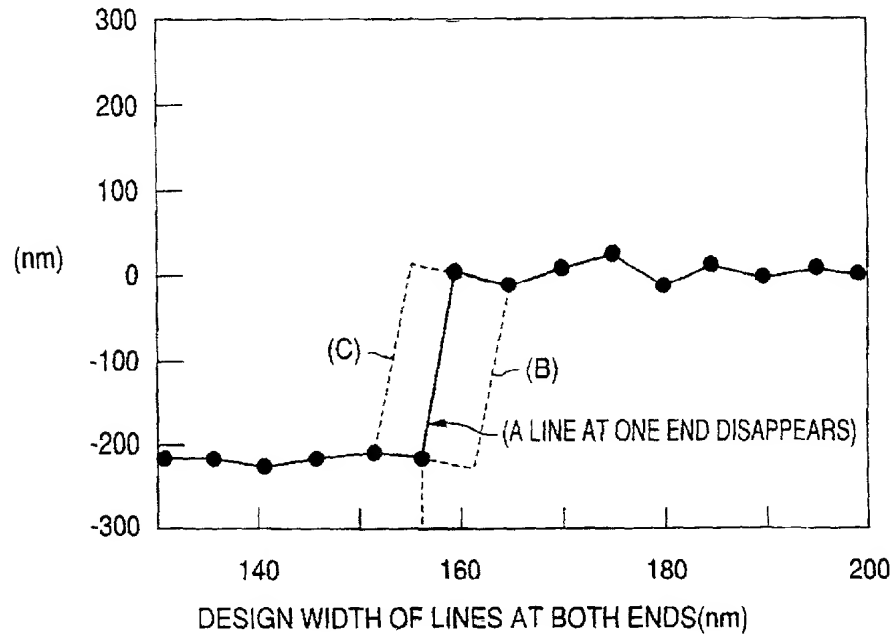


Fig.8

LINE WIDTH RELATED TO A MISSING  
LINE PATTERN AT ONE END

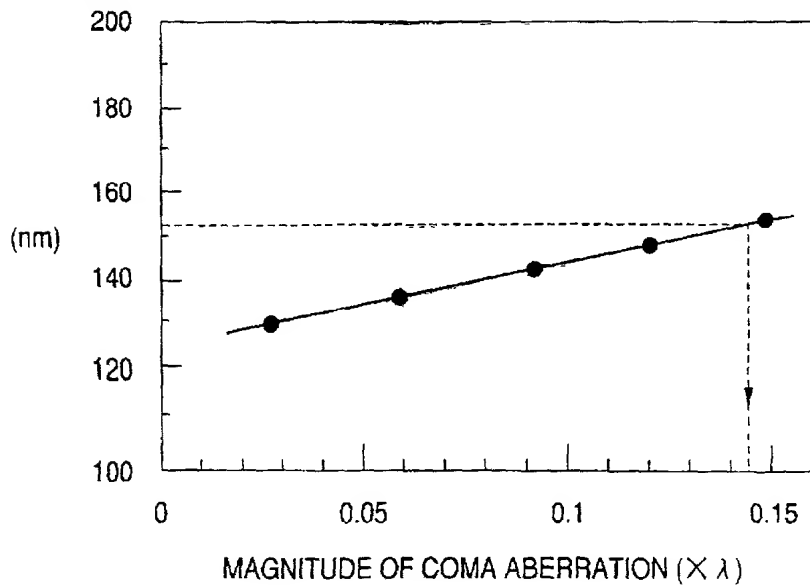


Fig.9

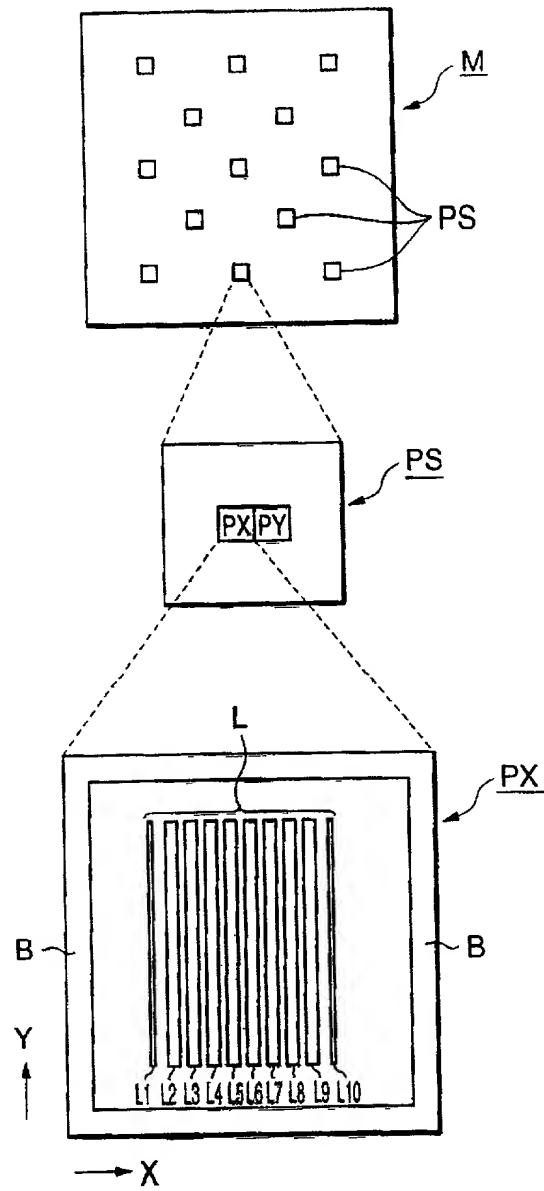




Fig.10(a)

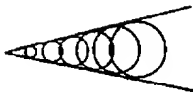


Fig.10(b)

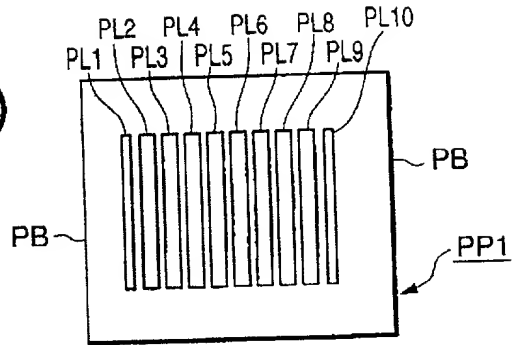


Fig.10(c)

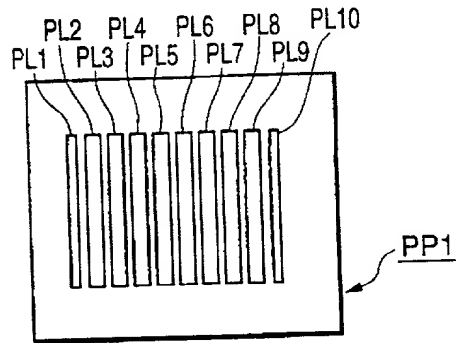


Fig.10(d)

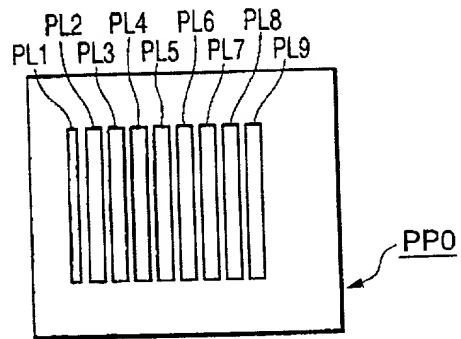


Fig.10(e)

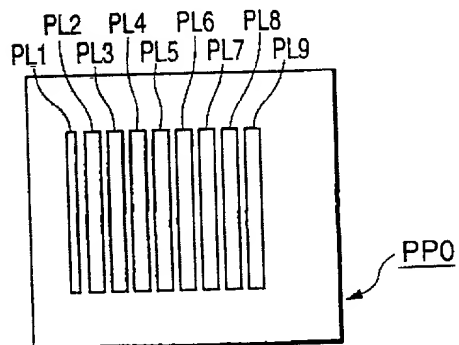


Fig.11

RELATIVE POSITIONAL DEVIATION  
(RESULT OF OVERLAY MEASUREMENT)

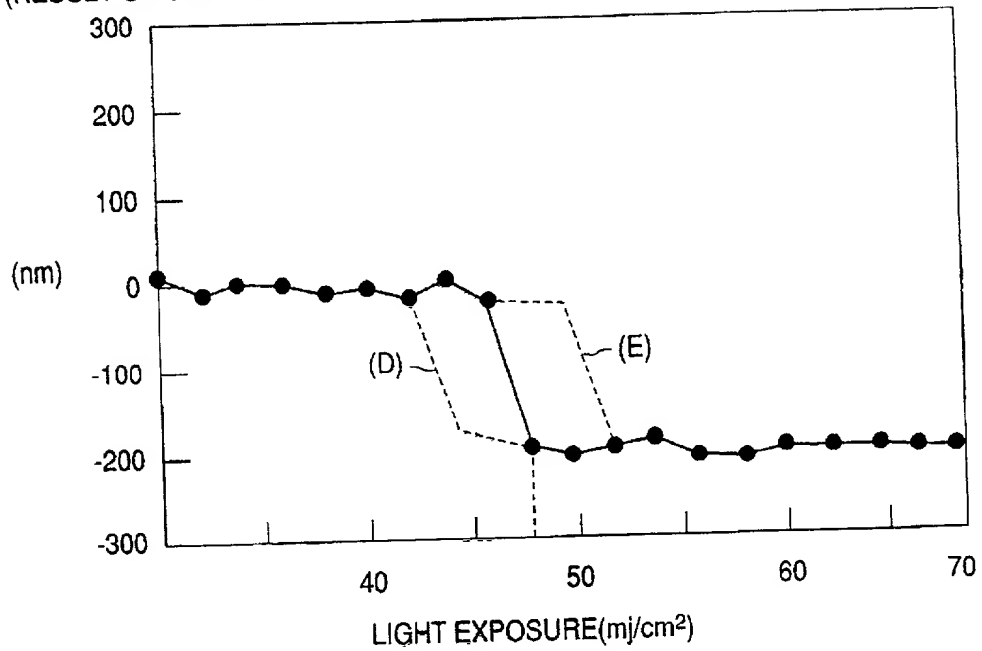


Fig.12

RIGHT EXPOSURE RELATED TO A MISSING  
LINE PATTERN AT ONE END

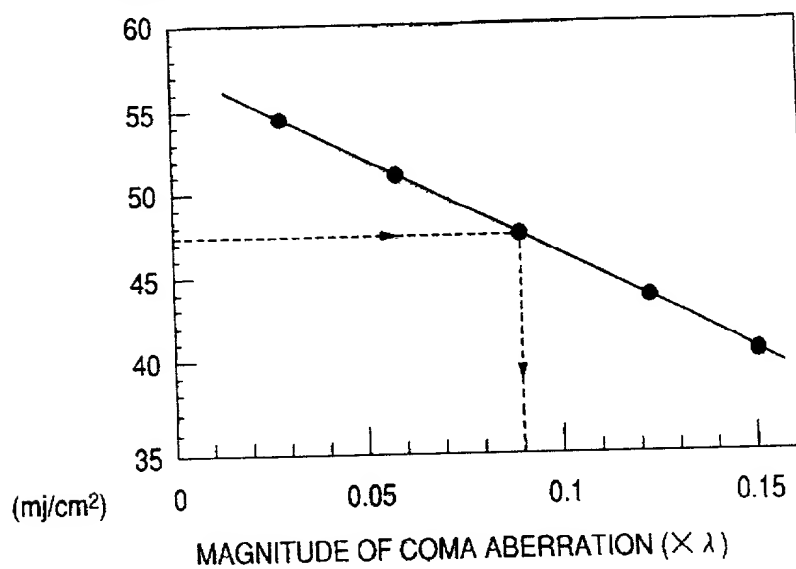


Fig.13(a)

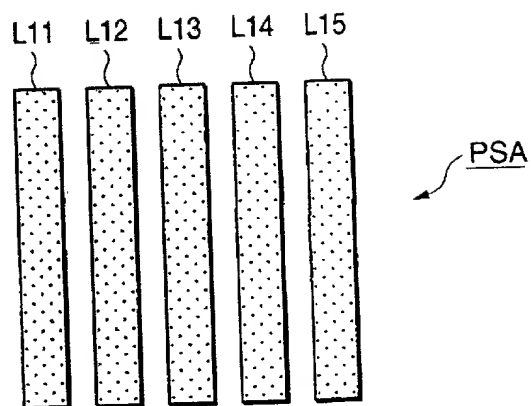


Fig.13(b)

